## Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in this application.

## **Listing of Claims:**

1. (Original) A method of manufacturing a micromechanical component, the method comprising:

providing a substrate having a front side and a back side;

patterning the front side of the substrate;

at least partially covering the patterned front side of the substrate with a protective layer containing germanium;

patterning the back side of the substrate; and

at least partially removing the protective layer containing germanium from the patterned front side of the substrate.

- 2. (Original) The method according to claim 1, wherein the substrate has a wafer substrate, a first sacrificial layer situated on the wafer substrate and a micromechanical function layer situated on the first sacrificial layer, the micromechanical function layer forming the front side and the wafer substrate forming the back side.
- 3. (Currently Amended) The A method according to claim 1 of manufacturing a micromechanical component, further the method comprising:

providing a substrate having a front side and a back side;

patterning the front side of the substrate;

at least partially covering the patterned front side of the substrate with a protective layer containing germanium;

patterning the back side of the substrate;

at least partially removing the protective layer containing germanium from the patterned front side of the substrate; and

forming a hard-surface mask on the front side of the substrate, the protective layer being formed selectively in openings in the hard-surface mask.

4. (Original) The method according to claim 3, further comprising applying the

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protective layer to an entire portion of the back side of the substrate.

5. (Currently Amended) The A method according to claim 1 of manufacturing a micromechanical component, further the method comprising:

providing a substrate having a front side and a back side;

patterning the front side of the substrate;

at least partially covering the patterned front side of the substrate with a protective layer containing germanium;

patterning the back side of the substrate;

at least partially removing the protective layer containing germanium from the patterned front side of the substrate;

forming a first hard-surface mask on the front side of the substrate; and forming the protective layer over an entire surface of the first hard-surface mask.

- 6. (Currently Amended) The method according to claim 5, further comprising forming the protective layer over <u>an entire surface of</u> a nucleation layer <del>over the entire surface</del>.
- 7. (Currently Amended) The method according to claim 4 <u>5</u>, further comprising: forming a second hard-surface mask on the back side of the substrate; and

etching a cavern into the back side when the front side is covered at least partially by the protective layer.

8. (Original) The method according to claim 7, further comprising:
after etching the cavern, removing the protective layer from the front side;
and

subsequently etching trenches in a micromechanical function layer via a first hard-surface mask.

9. (Currently Amended) The method according to claim 7, wherein the protective layer is also provided on the back side, and wherein the method further comprising comprises:

patterning the protective layer on the back side to forming form the second hard-

surface mask from the protective layer on the back side.

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